

**IN THE CLAIMS**

1. (Currently Amended) A method comprising:  
~~providing a coating over a wafer, wherein the coating comprises at least one characteristic of a single crystal;~~  
testing a semiconductor tool using the wafer; and  
~~refreshing replacing at least a portion of the coating of the wafer with a layer of coating, wherein each coating comprises at least one characteristic of a single crystal structure.~~
2. (Currently Amended) The method of Claim 1, wherein the testing comprises:  
providing a film over the surface coating of the wafer; and  
testing at least one characteristic of the film.
3. (Original) The method of Claim 2, wherein the at least one characteristic of the film comprises uniformity of thickness of the film.
4. (Original) The method of Claim 2, wherein the at least one characteristic of the film comprises grain size.
5. (Original) The method of Claim 2, wherein the at least one characteristic of the film comprises ability to polish the wafer.
6. (Original) The method of Claim 1, further comprising  
testing surface contaminant adding properties of the semiconductor tool.

7. (Original) The method of Claim 6, wherein the testing surface contaminant adding properties comprises testing light scattering properties of a surface of the wafer.
8. (Currently Amended) The method of Claim 1, wherein the ~~single crystal~~ at least one characteristic of a single crystal structure comprises insignificant distortion of an angle of refraction of incident light.

**Claims 9 – 21 (cancelled)**

22. (New) The method of Claim 2, wherein the at least one characteristic of the film comprises film thickness.
23. (New) The method of Claim 1, wherein the providing comprises:
  - providing a polysilicon layer; and
  - surface polishing the polysilicon layer.
24. (New) The method of Claim 1, wherein the replacing comprises:
  - mechanically grinding a portion of the coating;
  - providing a polysilicon layer; and
  - surface polishing the polysilicon layer.
25. (New) The method of Claim 1, further comprising removing contaminants from a surface of the coating of the wafer.

26. (New) A method comprising:  
replacing at least a portion of a coating of a wafer with a layer of coating, wherein each coating has at least one characteristic of a single crystal structure; and  
testing at least one characteristic of a semiconductor tool using the coated wafer.
27. (New) The method of Claim 26, wherein the replacing comprises:  
mechanically grinding the coating of the wafer;  
providing a polysilicon layer; and  
surface polishing the polysilicon layer.
28. (New) The method of Claim 27, wherein the replacing further comprises removing contaminants from a surface of the coating of the wafer.
29. (New) The method of Claim 26, wherein the testing comprises:  
providing a film over the coating of the wafer; and  
testing at least one characteristic of the film.
30. (New) The method of Claim 29, wherein the at least one characteristic of the film comprises uniformity of thickness of the film.
31. (New) The method of Claim 29, wherein the at least one characteristic of the film comprises grain size.

32. (New) The method of Claim 29, wherein the at least one characteristic of the film comprises film thickness.
33. (New) The method of Claim 26, further comprising testing surface contaminant adding properties of the semiconductor tool.
34. (New) The method of Claim 33, wherein the testing surface contaminant adding properties comprises testing light scattering properties of a surface of the wafer.
35. (New) The method of Claim 26, wherein the at least one characteristic of a single crystal structure comprises insignificant distortion of an angle of refraction of incident light.